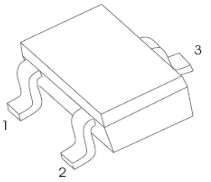
Plastic-Encapsulate Diodes

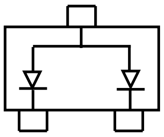
SWITCHING DIODE

SOT-523

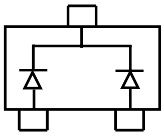


FEATURES

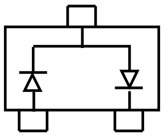
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56T Marking: A1



BAV70T Marking: A4



BAV99T Marking: A7

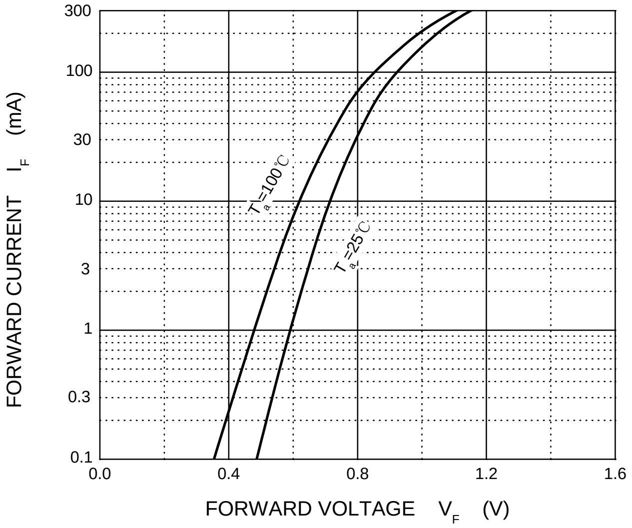
Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	85	V
Forward current	I_O	150	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55~+150	℃

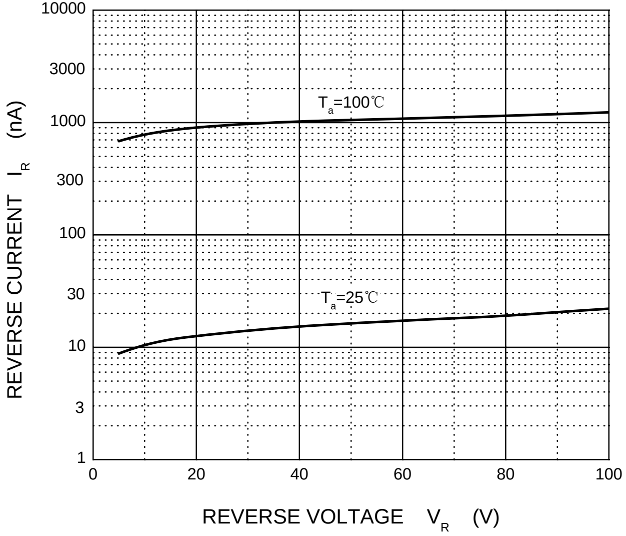
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 10μA	85		V
Reverse voltage leakage current	I_{R1}	V_R=75V		2	μA
	I_{R2}	V_R=25V		0.03	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Diode capacitance	C_D	V_R=0 f=1MHz		1.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R$=10mA $I_{rr}=0.1\times I_R$, $R_L=100\Omega$		4	ns

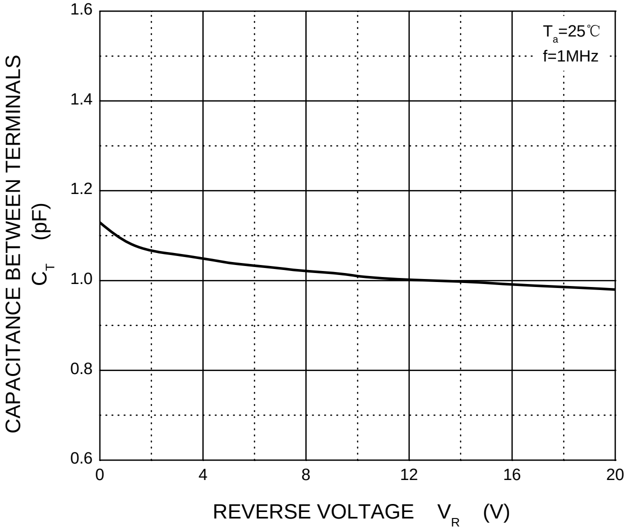
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve